

## **INCHANGE SEMICONDUCTOR**

## **Isc N-Channel MOSFET Transistor**

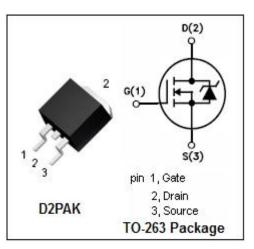
## STB75NF75T4

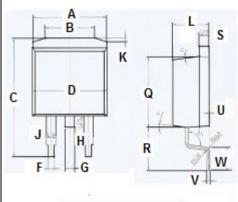
## • FEATURES

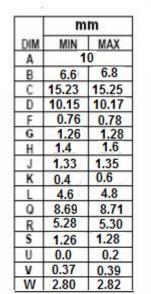
- With To-263(D2PAK) package
- Excellent switching performance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

Switching applications







### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL           | PARAMETER   | VALUE   | UNIT |  |
|------------------|---|---------|------|--|
| V <sub>DSS</sub> | Drain-Source Voltage  | V       |      |  |
| $V_{GSS}$        | Gate-Source Voltage ±20   |         | V    |  |
| ID               | Drain Current-Continuous@Tc=25°C 80   ( T_J=175°C ) Tc=125°C 70 |         | А    |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed                                     | 320     | А    |  |
| P <sub>D</sub>   | Total Dissipation @Tc=25°C 300                                  |         | W    |  |
| T <sub>ch</sub>  | Max. Operating Junction Temperature 175                         |         | °C   |  |
| T <sub>stg</sub> | Storage Temperature   | -55~175 | °C   |  |

#### THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                             |      | UNIT         |  |
|-----------|---------------------------------------|------|--------------|--|
| Rth(ch-c) | Channel-to-case thermal resistance    | 2.14 | °C <b>/W</b> |  |
| Rth(ch-a) | Channel-to-ambient thermal resistance | 100  | °C/W         |  |

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## **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL               | PARAMETER                      | CONDITIONS   | MIN | ТҮР | МАХ     | UNIT |
|----------------------|--------------------------------|--|-----|-----|---------|------|
| BV <sub>DSS</sub>    | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA   | 75  |     |         | v    |
| V <sub>GS</sub> (th) | Gate Threshold Voltage         | V <sub>DS</sub> = ±20V; I <sub>D</sub> =0.25mA   | 2   |     | 4       | v    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =40A   |     | 9.5 | 11      | mΩ   |
| I <sub>GSS</sub>     | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V   |     |     | ±0.1    | μ Α  |
| I <sub>DSS</sub>     | Drain-Source Leakage Current   | V <sub>DS</sub> = 75V; V <sub>GS</sub> = 0V; T <sub>J</sub> =25°C<br>T <sub>J</sub> =125°C |     |     | 1<br>10 | μ Α  |
| V <sub>SDF</sub>     | Diode forward voltage          | I <sub>SD</sub> =80A, V <sub>GS</sub> = 0 V  |     |     | 1.5     | V    |

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